

## In the Claims

Claims 1-34: (Cancelled).

35. (Currently Amended): A method forming a local interconnect comprising:

forming at least two transistor gates over a semiconductor substrate;

depositing a local interconnect layer to overlie at least one of the transistor gates and interconnect at least one source/drain region of proximate one of the transistor gates with semiconductor substrate material proximate another of the transistor gates;

implanting ~~conductivity-enhancing impurity~~ at least one dopant into the local interconnect layer in at least two implanting steps, one of the two ~~implantings~~ implanting steps providing a peak implant location in a first portion of the layer which is deeper ~~into~~ within the layer than ~~the other a~~ a peak implant of the other implanting step; and

diffusing ~~conductivity-enhancing impurity~~ at least some of the dopant from the local interconnect layer into semiconductor substrate material therebeneath.

36. (Currently Amended): The method of claim 35 comprising conducting the one implanting step relative to another portion of the local interconnect layer to have a peak implant location ~~which is~~ extending through said layer and ~~within~~ into the semiconductor substrate material therebeneath.

37. (Currently Amended): A method of forming a local interconnect comprising:

forming at least two transistor gates over a semiconductor substrate;

depositing a local interconnect layer to overlie at least one of the transistor gates and interconnect at least one source/drain region ~~of~~ proximate one of the transistor gates with semiconductor substrate material proximate another of the transistor gates; and

implanting ~~conductivity-enhancing impurity~~ at least one dopant through the local interconnect layer into semiconductor substrate material therebeneath.

38. (Currently Amended): The method of claim 37 further comprising in another implanting step separate from said implanting, implanting ~~conductivity-enhancing impurity~~ at least one dopant to a peak concentration location which is entirely within ~~the~~ the local interconnect layer.

Claims 39-63 (Cancelled).

64. (New): The method of claim 35 wherein the semiconductor substrate material comprises bulk substrate material.

65. (New): The method of claim 35 wherein the semiconductor substrate material comprises bulk monocrystalline silicon.

66. (New): The method of claim 35 wherein the two implanting steps implant dopants which are of the same conductivity type.

67. (New): The method of claim 35 wherein the two implanting steps implant dopants which are of different conductivity type.

68. (New): The method of claim 35 wherein the two transistor gates each comprise an insulative cap, and wherein the deeper one implanting step also provides a peak implant location which is received within the insulative cap of at least one of the transistor gates.

69. (New): The method of claim 68 wherein the deeper one implanting step also provides a peak implant location which is received within the insulative cap of both of the transistor gates.

70. (New): The method of claim 35 wherein the two transistor gates each comprise at least one anisotropically etched insulative sidewall spacer, and wherein the deeper one implanting step also provides a peak implant location which is received within at least one of the anisotropically etched insulative sidewall spacers.

71. (New): The method of claim 70 wherein the deeper one implanting step also provides a peak implant location which is received within insulative sidewall spacers of both of the transistor gates.

72. (New): The method of claim 70 wherein the two transistor gates each comprise an insulative cap, and wherein the deeper one implanting step also provides a peak implant location which is received within the insulative cap of at least one of the transistor gates.

73. (New): The method of claim 72 wherein the deeper one implanting step also provides a peak implant location which is received within the insulative cap of both of the transistor gates.

74. (New): The method of claim 37 wherein the semiconductor substrate material comprises bulk substrate material.

75. (New): The method of claim 37 wherein the semiconductor substrate material comprises bulk monocrystalline silicon.

76. (New): The method of claim 37 wherein the two transistor gates each comprise an insulative cap, and wherein the implanting also provides a peak implant location which is received within the insulative cap of at least one of the transistor gates.

77. (New): The method of claim 76 wherein the implanting also provides a peak implant location which is received within the insulative cap of both of the transistor gates.

78. (New): The method of claim 37 wherein the two transistor gates each comprise at least one anisotropically etched insulative sidewall spacer, and wherein the implanting also provides a peak implant location which is received within at least one of the anisotropically etched insulative sidewall spacers.

79. (New): The method of claim 78 wherein the implanting also provides a peak implant location which is received within insulative sidewall spacers of both of the transistor gates.

80. (New): The method of claim 78 wherein the two transistor gates each comprise an insulative cap, and wherein the implanting also provides a peak implant location which is received within the insulative cap of at least one of the transistor gates.

81. (New): The method of claim 80 wherein the implanting also provides a peak implant location which is received within the insulative cap of both of the transistor gates.